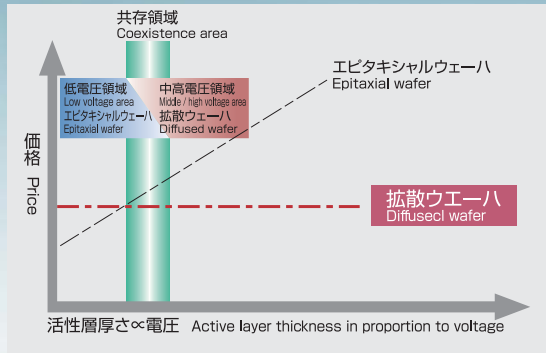


拡散ウェーハ

Diffused Wafers

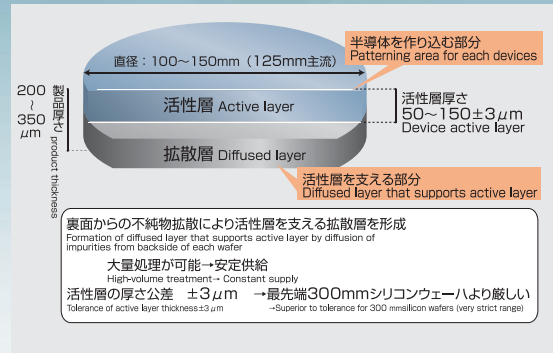
コンセプト Concept

耐高電圧領域の個別半導体素子用シリコンウェーハ
Silicon wafer for high voltage individual semiconductor devices



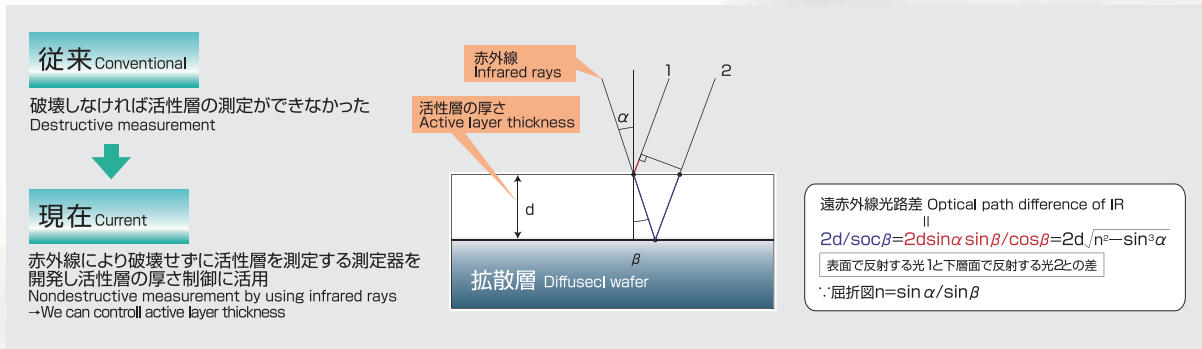
代表的製品・特長 Features

公差 $\pm 3\mu\text{m}$ 以内の活性層の厚さを実現
Tolerance of active layer thickness
→ within $\pm 3\mu\text{m}$



中核技術 Core technology

赤外線を用いた「非破壊」での活性層測定技術
Nondestructive measurement of active layer thickness by using infrared rays



今後の方向・計画 Future direction and plan

高品質を堅持し供給能力アップで市場拡大
Market expansion by high quality and increase of supply capacity

